

V_{DSS}	250V
$R_{DS(on)}$ (Max.)	8.8Ω
I_D	0.5A
P_D	1.0W

●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Drive circuits can be simple.
- 4) Parallel use is easy.
- 5) Pb-free lead plating ; RoHS compliant

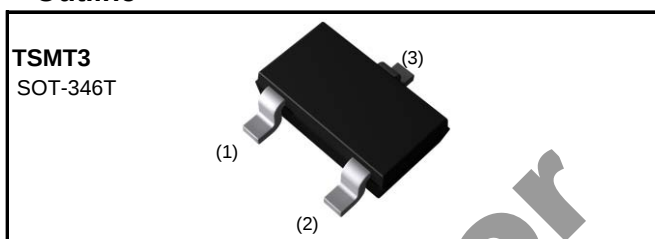
●Application

Switching Power Supply
Automotive Motor Drive
Automotive Solenoid Drive

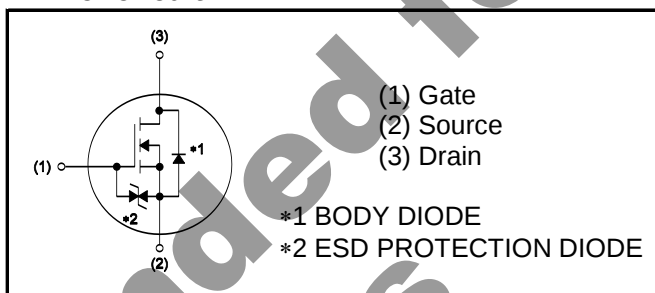
●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	250	V
Continuous drain current	$T_c = 25^\circ\text{C}$	I_D^{*1}	± 0.5	A
	$T_c = 100^\circ\text{C}$	I_D^{*1}	± 0.27	A
Pulsed drain current		$I_{D,pulse}^{*2}$	± 2.0	A
Gate - Source voltage		V_{GSS}	± 20	V
Power dissipation		P_D^{*3}	1.0	W
		P_D^{*4}	0.54	W
Junction temperature		T_j	150	$^\circ\text{C}$
Range of storage temperature		T_{stg}	-55 to +150	$^\circ\text{C}$

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3,000
	Taping code	TL
	Marking	EE

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA}^{*3}	-	-	125	°C/W
	R_{thJA}^{*4}	-	-	232	°C/W

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	250	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 250V, V_{GS} = 0V$ $T_j = 25^\circ\text{C}$	-	-	25	μA
		$V_{DS} = 250V, V_{GS} = 0V$ $T_j = 125^\circ\text{C}$	-	-	100	
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	1.0	-	3.0	V
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS} = 10V, I_D = 0.25A$	-	6.8	8.8	Ω
		$V_{GS} = 4.5V, I_D = 0.25A$		7.2	9.4	
		$V_{GS} = 4V, I_D = 0.25A$		7.4	9.6	
		$V_{GS} = 10V, I_D = 0.25A$ $T_j = 125^\circ\text{C}$	-	12.8	18.0	
Forward transfer admittance	g_{fs}	$V_{DS} = 10V, I_D = 0.25A$	0.21	0.42	-	S

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	70	-	pF
Output capacitance	C_{oss}	$V_{DS} = 25V$	-	10	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	3	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx 125V, V_{GS} = 10V$	-	6	-	ns
Rise time	t_r^{*5}	$I_D = 0.25A$	-	10	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 500\Omega$	-	21	-	
Fall time	t_f^{*5}	$R_G = 10\Omega$	-	90	-	

●Gate Charge characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*5}	$V_{DD} \approx 125V$	-	3.5	-	nC
Gate - Source charge	Q_{gs}^{*5}	$I_D = 0.5A$	-	0.55	-	
Gate - Drain charge	Q_{gd}^{*5}	$V_{GS} = 10V$	-	1.0	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} \approx 125V, I_D = 0.5A$	-	3.0	-	V

●Body diode electrical characteristics (Source-Drain)($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous source current	I_S^{*1}	$T_c = 25^\circ\text{C}$	-	-	0.5	A
Pulsed source current	I_{SM}^{*2}		-	-	2.0	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0V, I_S = 0.5A$	-	-	1.2	V
Reverse recovery time	t_{rr}^{*5}	$I_S = 0.25A$	-	60	-	ns
Reverse recovery charge	Q_{rr}^{*5}	$di/dt = 100A/\mu s$	-	60	-	nC

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu s$, Duty cycle $\leq 1\%$

*3 Mounted on a ceramic board (30×30×0.8mm)

*4 Mounted on a FR4 (12×20×0.8mm)

*5 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

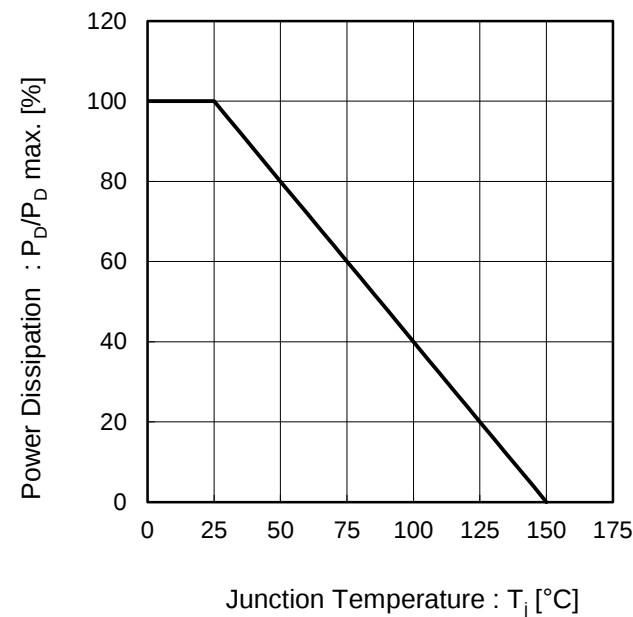
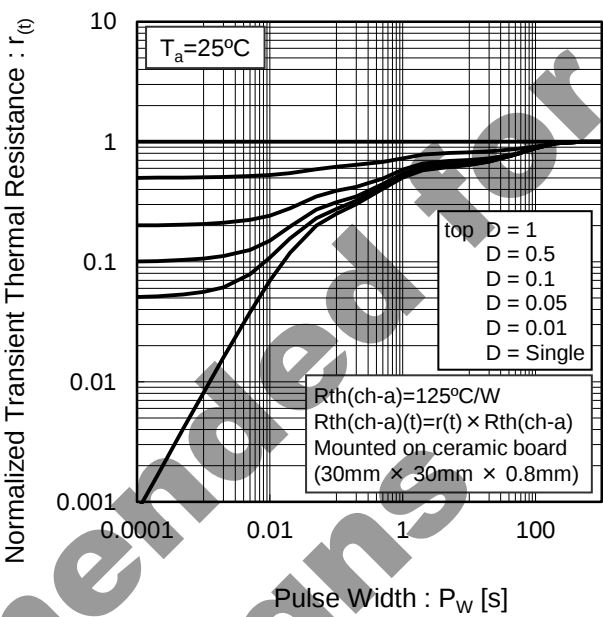


Fig.2 Normalized Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.3 Typical Output Characteristics(I)

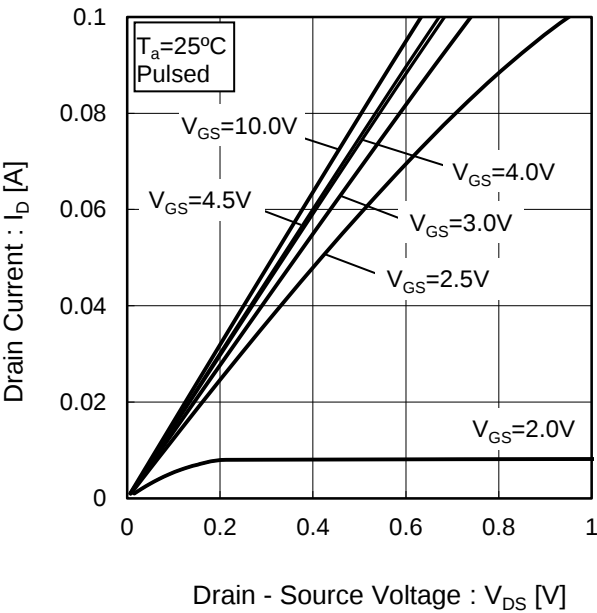
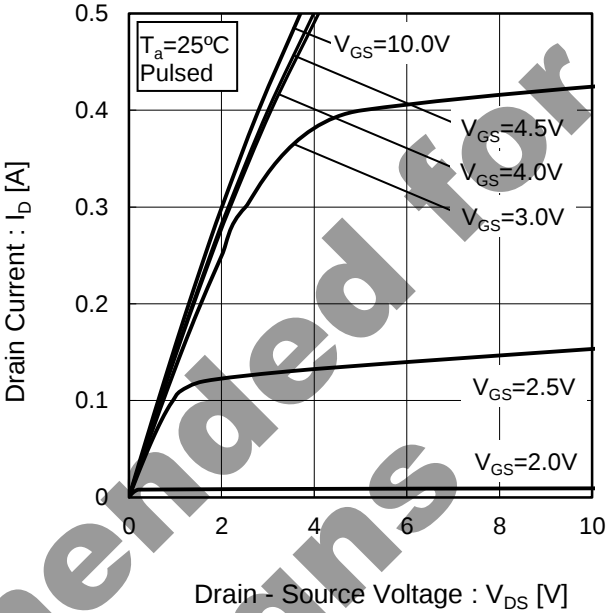


Fig.4 Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.5 Breakdown Voltage
vs. Junction Temperature

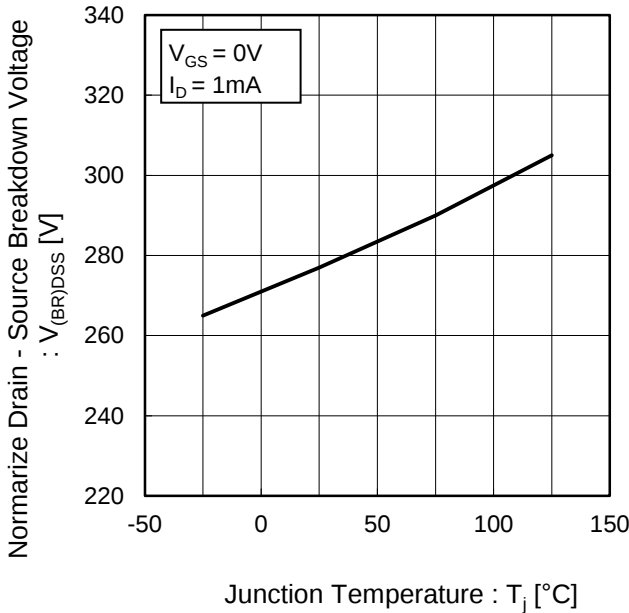


Fig.6 Typical Transfer Characteristics

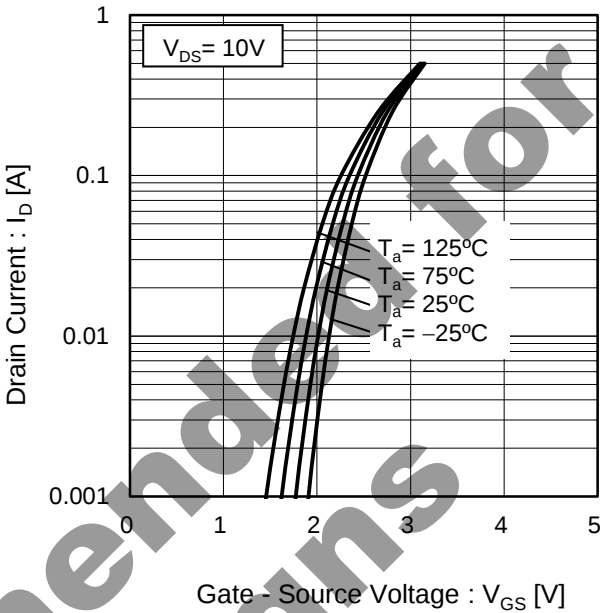


Fig.7 Gate Threshold Voltage
vs. Junction Temperature

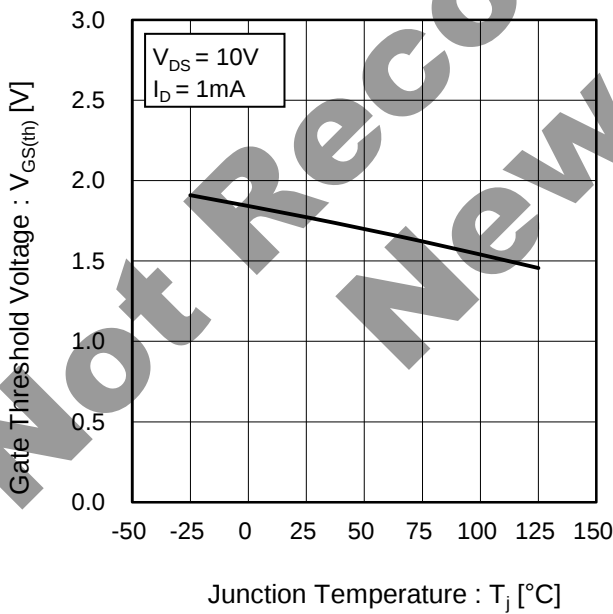
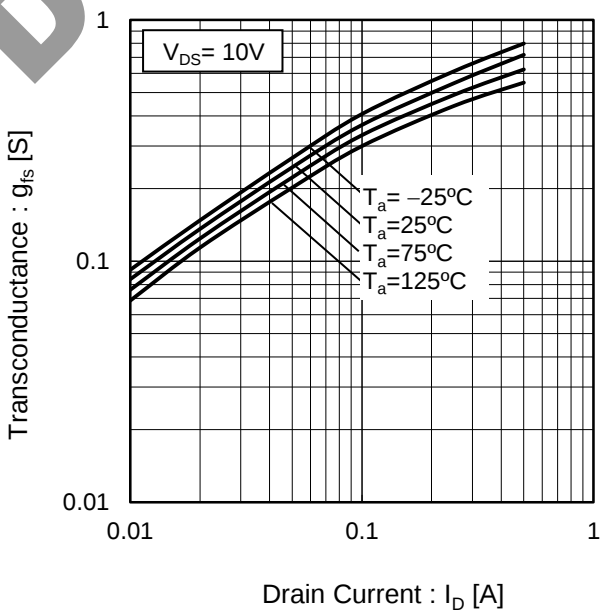


Fig.8 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.9 Static Drain - Source On - State Resistance vs. Gate Source Voltage

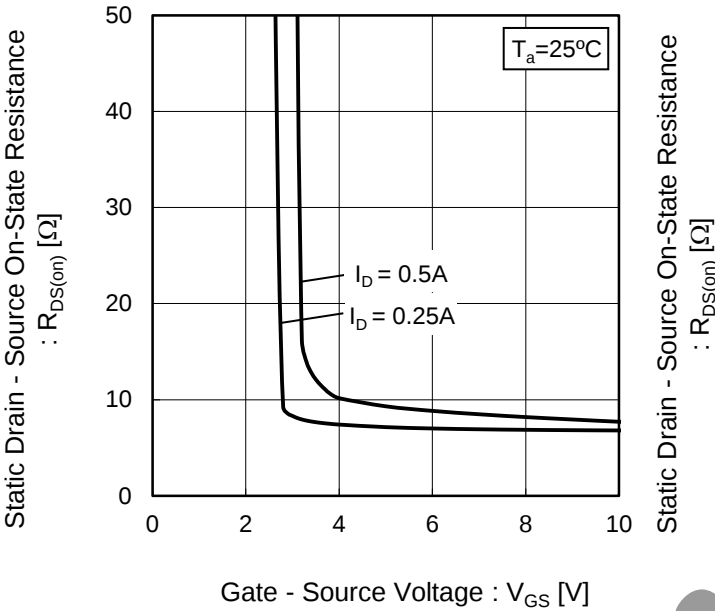


Fig.10 Static Drain - Source On - State Resistance vs. Drain Current(I)

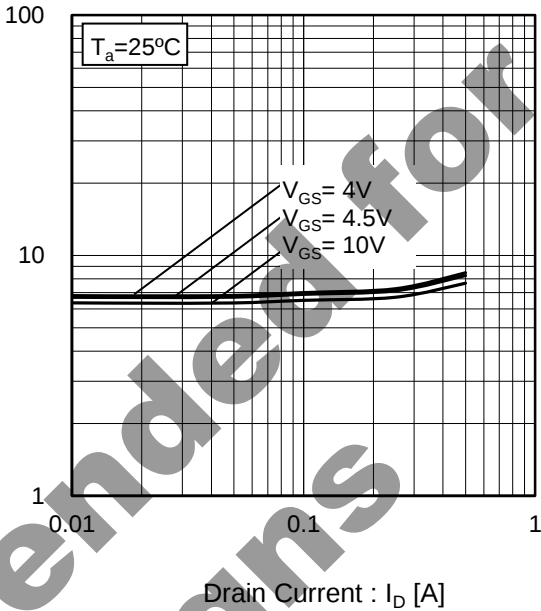
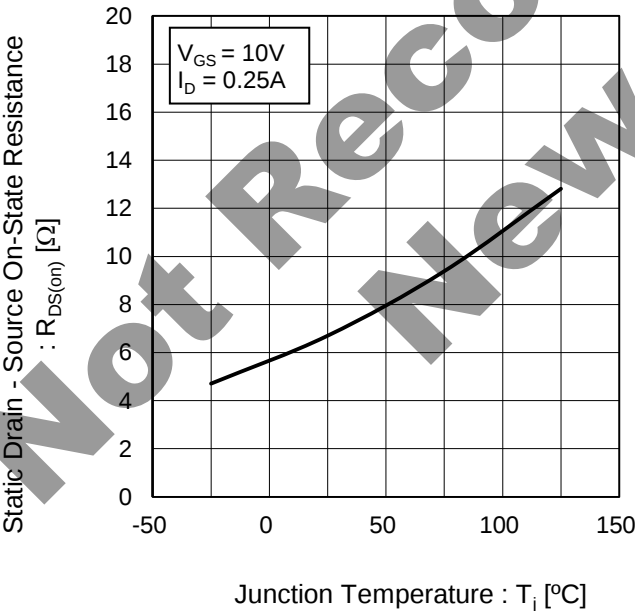


Fig.11 Static Drain - Source On - State Resistance vs. Junction Temperature



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Drain Current(I)

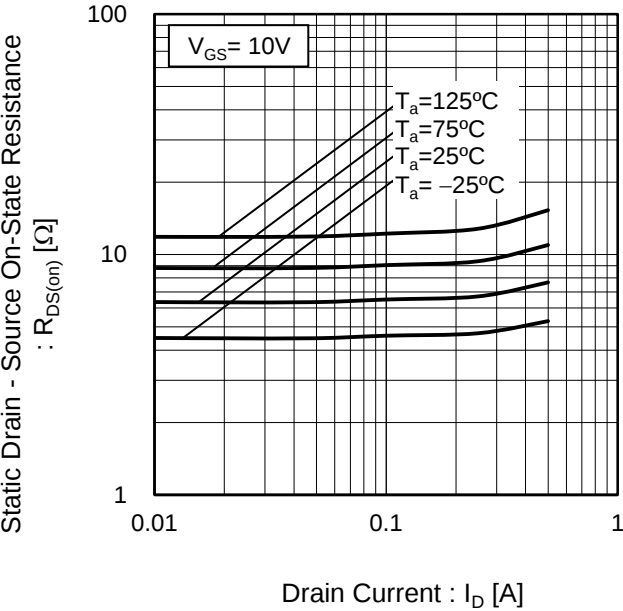


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(II)

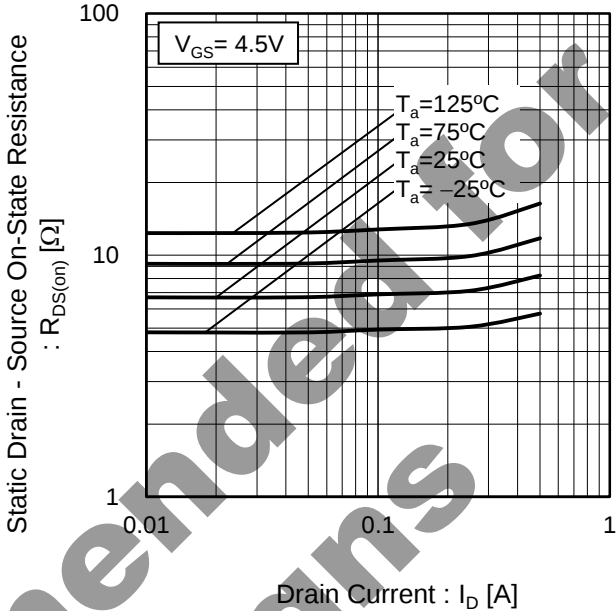


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(III)

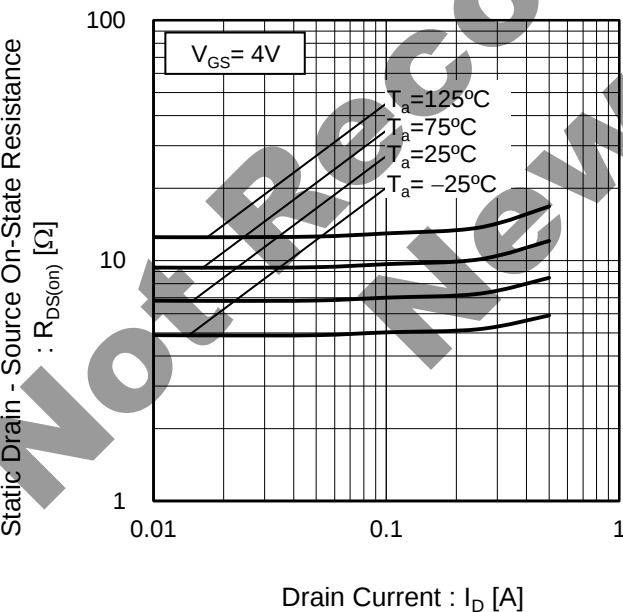
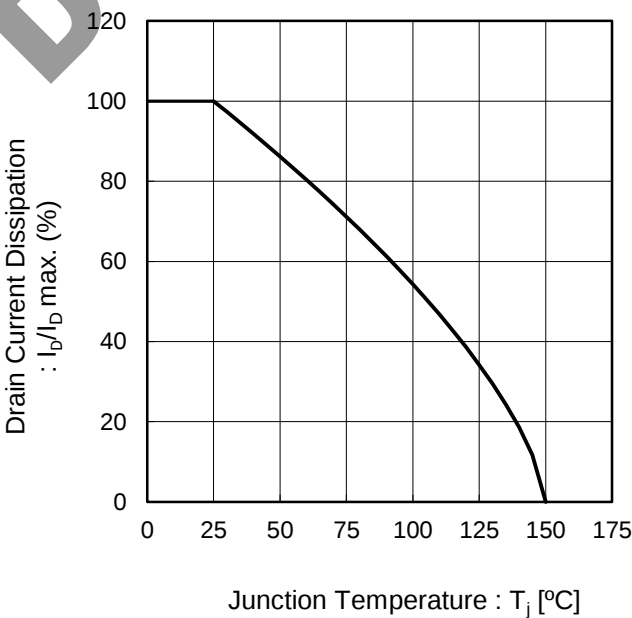


Fig.15 Drain Current Derating Curve



●Electrical characteristic curves

Fig.16 Typical Capacitance vs. Drain - Source Voltage

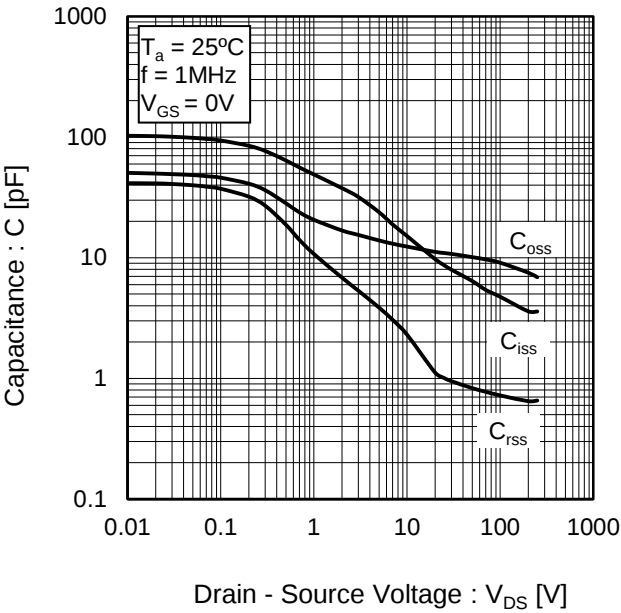


Fig.17 Switching Characteristics

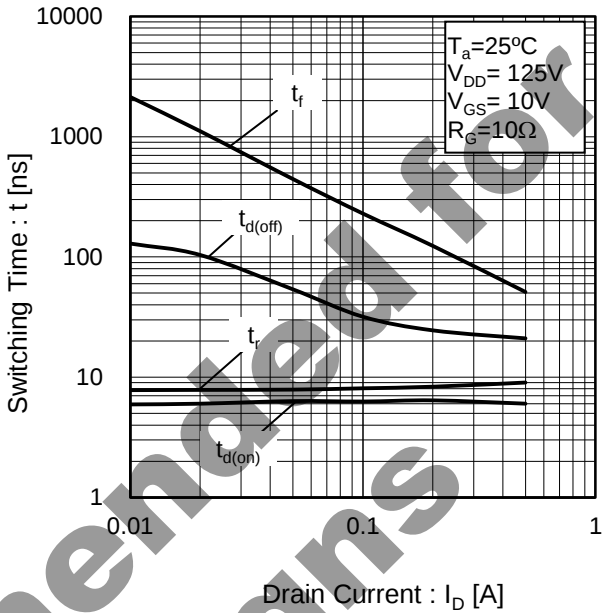
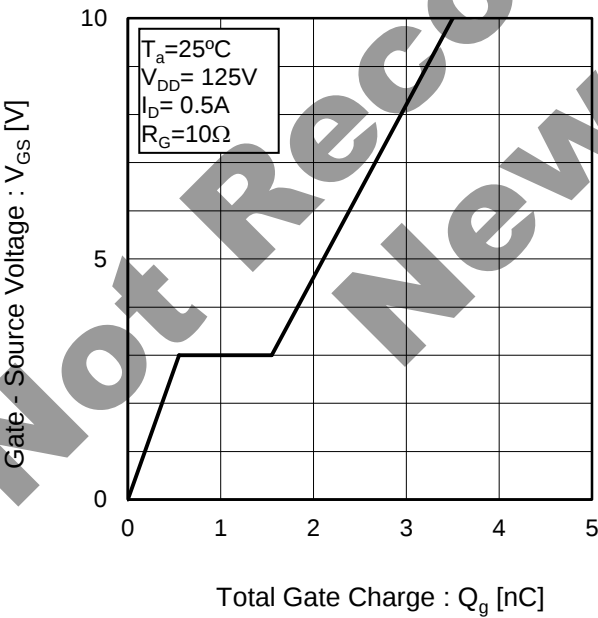


Fig.18 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.19 Source Current
vs. Source - Drain Voltage

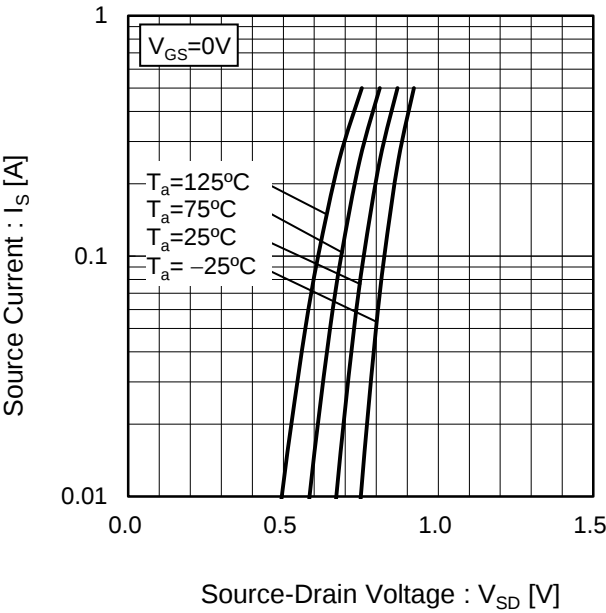
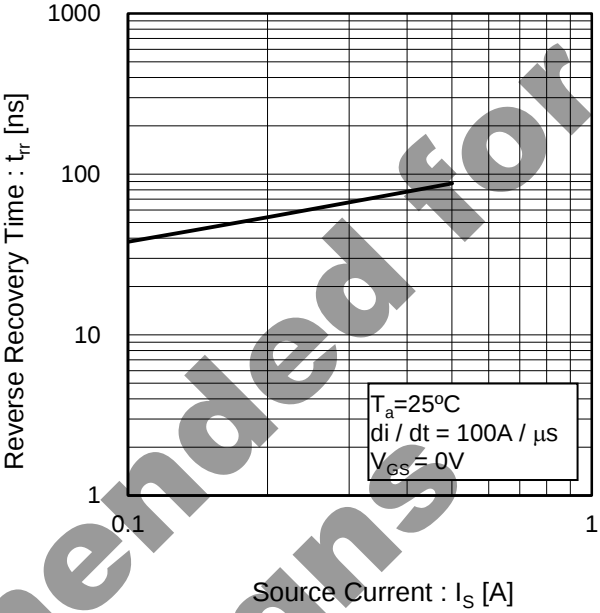


Fig20 Reverse Recovery Time
vs.Source Current



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

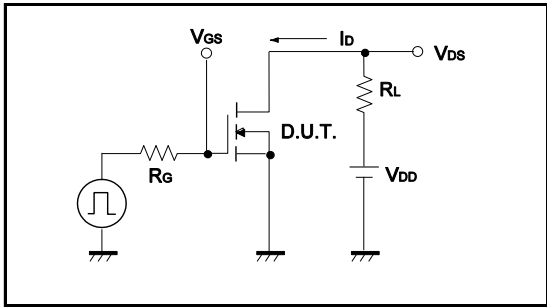


Fig.1-2 Switching Waveforms

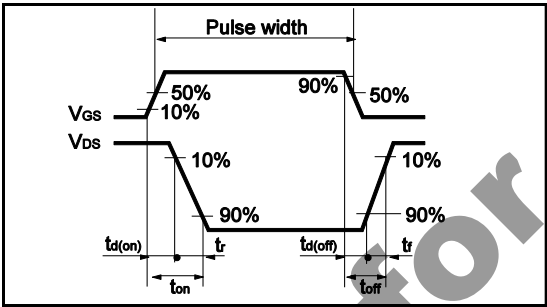


Fig.2-1 Gate Charge Measurement Circuit

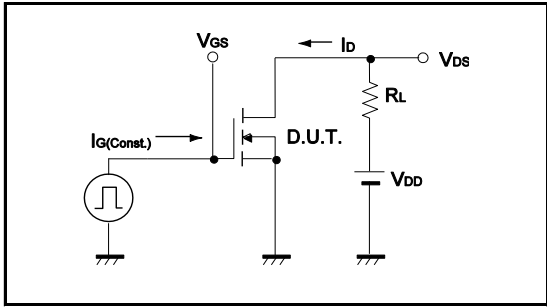
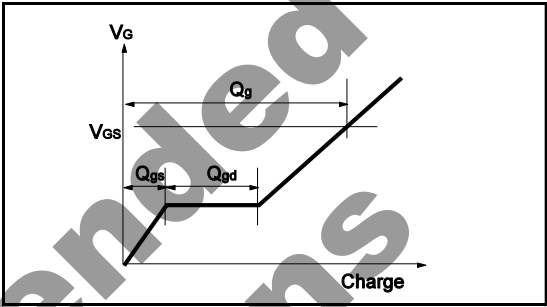
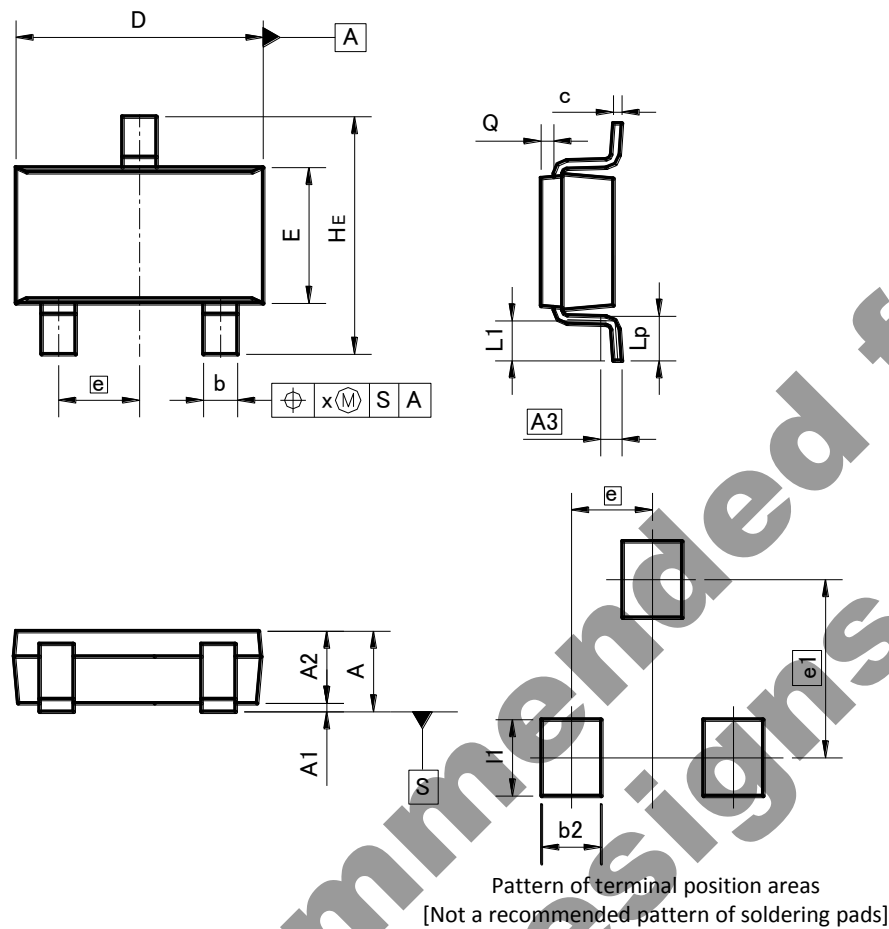


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit : mm)

TSMT3



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	—	1.00	—	0.039
A1	0.00	0.10	0.000	0.004
A2	0.75	0.95	0.030	0.037
A3	0.25		0.010	
b	0.35	0.50	0.014	0.020
c	0.10	0.26	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.010
x	—	0.20	—	0.008

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	—	0.70	—	0.028
e1	2.10		0.083	
l1	—	0.90	—	0.035

Dimension in mm / inches

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